

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (currently amended): A method for forming MOSFETs, comprising:

providing a semiconductor substrate having a source region, a channel region, and a drain region, wherein the channel region resides between the source and drain regions and a gate region resides over the channel region of the substrate;

forming a silicon-germanium layer within said substrate in each of the source and drain regions in the substrate, the silicon-germanium layer configured to exert a compressive stress in the channel region of the substrate;

~~forming, in the substrate, a source in the source region and a drain in the drain region;~~

forming a silicon layer outwardly from said substrate and the silicon-germanium layer in each of the source and drain regions; and

forming a silicide layer in each of the source and drain regions.

Claim 2 (currently amended): The method of Claim 1, wherein forming the silicide layer comprises:

depositing a reactive metal outwardly from the silicon layer and the silicon-germanium layer in each of the source and drain regions;

reacting the reactive metal with at least the silicon layer; and

selectively removing non-reacted reactive metal from the substrate.

Claim 3 (original): The method of Claim 2, wherein the reactive metal is selected from the group consisting of titanium, cobalt, nickel, and tungsten.

Claim 4 (currently amended): The method of Claim 1, wherein forming the silicide layer comprises:

depositing a reactive metal outwardly from the silicon layer and the silicon-germanium layer in each of the source and drain regions;

reacting the reactive metal with the silicon layer and a portion of the silicon-germanium layer; and

selectively removing non-reacted reactive metal from the substrate.

Claim 5 (original): The method of Claim 4, wherein the reactive metal is selected from the group consisting of titanium, cobalt, nickel, and tungsten.

Claim 6 (canceled)

Claim 7 (canceled)

Claim 8 (original): The method of Claim 1, wherein the silicon layer has a thickness between approximately 25 Å and 150 Å.

Claim 9 (original): The method of Claim 1, wherein the silicon layer has a thickness of approximately 75 Å.

Claim 10 (original): The method of Claim 1, wherein the silicon-germanium layer has a thickness between approximately 200 Å and 300 Å.

Claim 11 (original): The method of Claim 1, wherein the silicon-germanium layer is an epitaxial layer.

Claim 12 (currently amended): A method for forming MOSFETs, comprising:
providing a substrate having a source region, a gate region, and a drain region;
forming, within ~~in~~ the substrate, a ~~an~~ epitaxial silicon-germanium region ~~layer~~ in each of the source and drain regions;
~~forming, in the substrate, a source in the source region and a drain in the drain region;~~
forming a silicon layer outwardly from the substrate and the silicon-germanium layer in each of the source and drain regions, the silicon layer having a thickness between approximately 25 Å and 150 Å;
depositing a reactive metal outwardly from the silicon layer in each of the source and drain regions;
reacting the reactive metal with at least a portion of the silicon layer; and
selectively removing non-reacted reactive metal from the substrate to form a silicide layer in each of the source and drain regions.

Claim 13 (original): The method of Claim 12, wherein the reactive metal is selected from the group consisting of titanium, cobalt, nickel, and tungsten.

Claim 14 (original): The method of Claim 12, wherein reacting the reactive metal with at least a portion of the silicon layer comprises reacting the reactive metal with the whole silicon layer and a portion of the silicon-germanium layer.

Claim 15 (original): The method of Claim 12, wherein the silicon layer has a thickness of approximately 75 Å.

Claim 16 (original): The method of Claim 12, wherein the silicon-germanium layer has a thickness between approximately 200 Å and 300 Å.

Claim 17 (withdrawn): A system for forming MOSFETs, comprising:
a substrate having a source region, a gate region, and a drain region;
an epitaxial silicon-germanium layer formed in each of the source and drain regions;
a source formed in the source region;
a drain formed in the drain region;
a silicon layer disposed outwardly from the silicon-germanium layer in each of the source and drain regions; and
a reactive metal layer formed in each of the source and drain regions.

Claim 18 (withdrawn): The system of Claim 18, wherein the silicon-germanium layer in each of the source and drain regions is formed within the substrate.

Claim 19 (withdrawn): The system of Claim 18, wherein the silicon-germanium layer in each of the source and drain regions is formed outwardly from the substrate.

Claim 20 (withdrawn): The system of Claim 18, wherein the silicon layer has a thickness between approximately 25 Å and 150 Å.